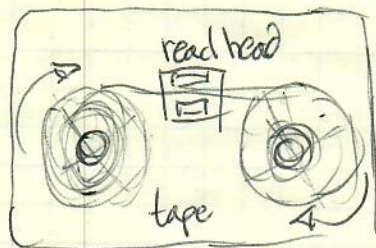


Random Access Memories (RAM) Use Verilog

The "random" in RAM is a reference to the access time to retrieve a byte at a random location (address), being independent of bytes location. First mass storage devices were tape drives. The time to access a byte depends on the physical distance between the current read location & the bytes location.



Types : Volatile / Non-Volatile
Static / Dynamic
Serial / Parallel

Power Removed
Refreshing
Moving bits in/out

NXM RAM

Data in : $\log_2(N)$ -bit address \vec{A}
Data out : M -bit bi-directional \vec{D}

Control : R/W & CS

States : None

Behavior :

A	CS	R/W	\vec{D}	Note
X	0	X	Z	hi impedance
A	1	0	$M[A] = D$	write
A	1	1	$D = M[A]$	read

RAM is collection of bits stored in words

8x4 RAM

Address	Contents
000	0110
001	1010
010	1101
011	0010
100	1000
101	0001
110	1101
111	1111

M[010] contains 1101

To read data

- ① Assert \bar{A} , $CS=1$, $R/\bar{W}=1$
- ② Wait
- ③ Read \bar{D}

To write data

- ① Assert \bar{A} \bar{D}
- ② Assert $CS=1$ $R/\bar{W}=0$
- ③ Wait

Size prefix	2^{10}	1 KB
	2^{20}	1 MB
	2^{30}	1 GB
	2^{40}	1 TB
	2^{50}	1 PB ?

How many address bits for 2GB memory?

$$2 * 1GB = 2^{31} \text{ bytes} \quad 31\text{-bits}$$

How many address bits for 512KB memory?

$$512 * 1KB = 2^{19} \text{ bytes} \quad 19\text{-bits}$$

Random Access Memory (RAM)

- Word set of bits that can ^{be} simultaneously manipulated.
- RAM is a collection of words, each stored at a unique address that can be retrieved (read) or overwritten (write).

N x M RAM

data in : $\log_2(N)$ bit address \vec{A}

data : M-bit bidirectional data \vec{D}

control : 1 bit R/W, CS

status : None

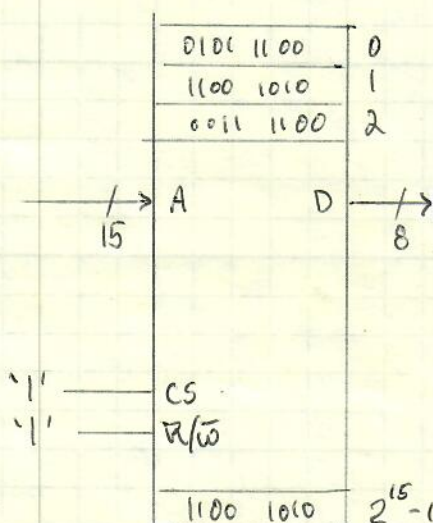
Behavior :

\vec{A}	CS	R/W	\vec{D}
X	0	X	Z
A	1	0	$M[A] = D$
A	1	1	$M[A]$

write
read

Example 32K x 8 RAM

32K = 2^{15} words each 8-bits



Size

1K	2^{10}
1M	2^{20}
1G	2^{30}
1T	2^{40}

$$2^N K =$$

$$2^N \cdot 2^{10} = 2^{10+N}$$